

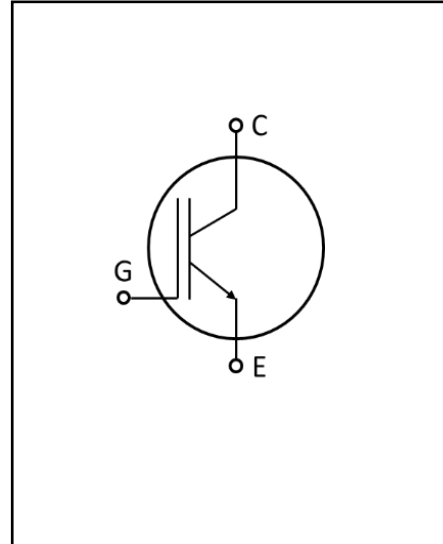
IGBT Chip

Features:

- 1200V Trench & Field stop technology
- Low Vcesat
- Positive temperature coefficient
- Easy paralleling

Applications:

- Power drives
- inverter



Mechanical parameters

Die size	6.48×6.48	mm ²
Emitter pad size	See chip drawing	
Gate pad size	1.18×0.77	
Area total	41.99	μm
Thickness	120	
Scribe line Size	80	mm
Wafer size	200	
Max. possible chips per wafer	632	
Passivation front side	Polyimide	
Pad metal	AlCu with Ti/TiN (5.0μm & 200A/700A)	
Backside metal	Al/Ti/Ni/Ag	

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-Emitter voltage	V_{CE}	1200	V
DC collector current	I_C	40	A
Operating junction temperature	T_{vj}	-40 ... +175	°C
Gate emitter voltage	V_{GE}	± 20	V
Short circuit data	t_{SC}	8	μs

Static Characteristics (tested on wafer), $T_{vj}=25^\circ C$

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Collector-Emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=1mA$	1200			V
Collector-Emitter saturation voltage	V_{CEsat}	$V_{GE}=15V, I_C=40A$		1.74	2.14	
Gate-Emitter threshold voltage	$V_{GE(th)}$	$I_C=1.5mA, V_{GE}=V_{CE}$	5.16	5.76	6.36	
Zero gate voltage collector current	I_{CES}	$V_{CE}=1200V, V_{GE}=0V$			10	μA
Gate-Emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V$			100	nA
Integrated gate resistor	r_G			None		Ω
Input capacitance	C_{ies}	$V_{CE}=25V, V_{GE}=0V,$ $f=100kHz$		2.70		nF
Reverse transfer capacitance	C_{res}			0.14		

Chip Drawing

